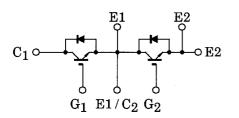
TOSHIBA GTR Module Silicon N Channel IGBT

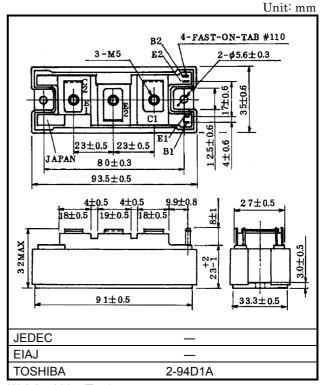
MG100J2YS50

High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance.
- Includes a complete half bridge in one package.
- Enhancement-mode.
- High speed : $t_f = 0.30 \mu s$ (Max) (I_C = 100A) $t_{rr} = 0.15 \mu s$ (Max) (I_F = 100A)
- Low saturation voltage
 - : V_{CE} (sat)=2.70V (Max) (I_C=100A)

Equivalent Circuit





Weight: 202g (Typ.)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	۱ _C	100	А	
	1ms	I _{CP}	200	~	
Forward current	DC	١ _F	100	A	
	1ms	I _{FM}	200		
Collector power dissipation (Tc=25°C)		P _C	450	W	
Junction temperature		Тj	150	°C	
Storage temperature range		T _{stg}	− 40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N∙m	

Maximum Ratings (Ta = 25°C)

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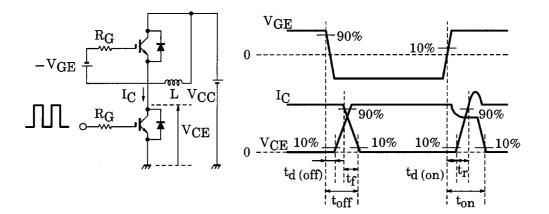
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Electrical Characteristics (Ta = 25°C)

С	haracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I _{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	_	—	±500	nA	
Collector cut-off current		ICES	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA	
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 10mA, V _{CE} = 5V	5.0	7.0	8.0	V	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 100A, V _{GE} = 15V	_	2.10	2.70	V	
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} =0, f = 1MHz	_	9000	_	pF	
Switching time	Turn-on delay time	t _{d (on)}		_	0.08	0.16	μs	
	Rise time	tr	Inductive load V _{CC} = 300V	_	0.12	0.24		
	Turn-on time	t _{on}	I _C = 100A	_	0.40	0.80		
	Turn-off delay time	t _{d (off)}	V _{GE} = ±15V R _G = 13Ω	_	0.20	0.40		
	Fall time	t _f	(Note 1)	_	0.15	0.30		
	Turn-off time	t _{off}			0.50	1.00		
Forward voltage		٧F	I _F = 100A, V _{GE} = 0	_	2.30	3.00	V	
Reverse recovery time		t _{rr}	I _F = 100A, V _{GE} = -10V di / dt = 100A / μs	_	0.08	0.15	μs	
Thermal resistance		R _{th (j-c)}	Transistor stage	_	_	0.28	°C/W	
			Diode stage	—	—	0.69	C/W	

Note 1: Switching time test circuit & timing chert

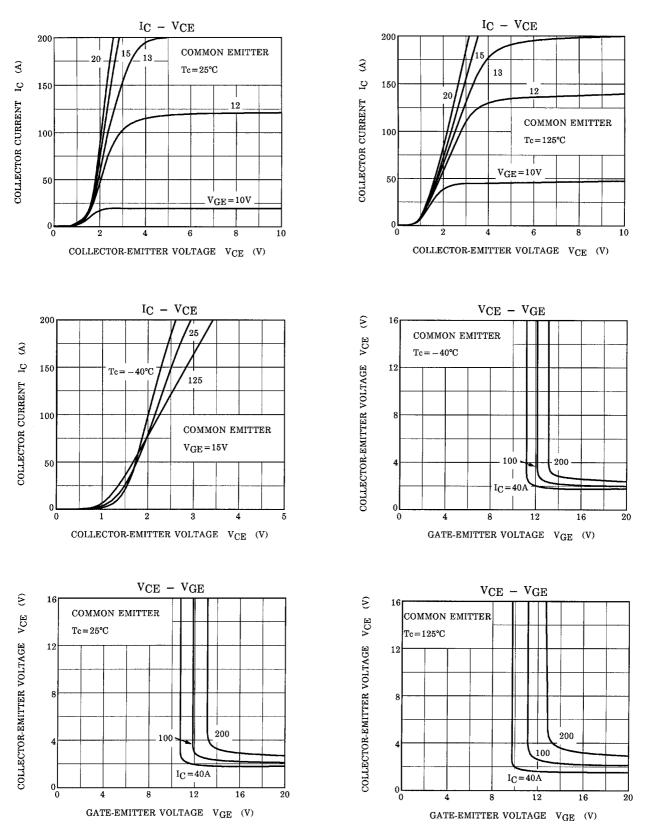


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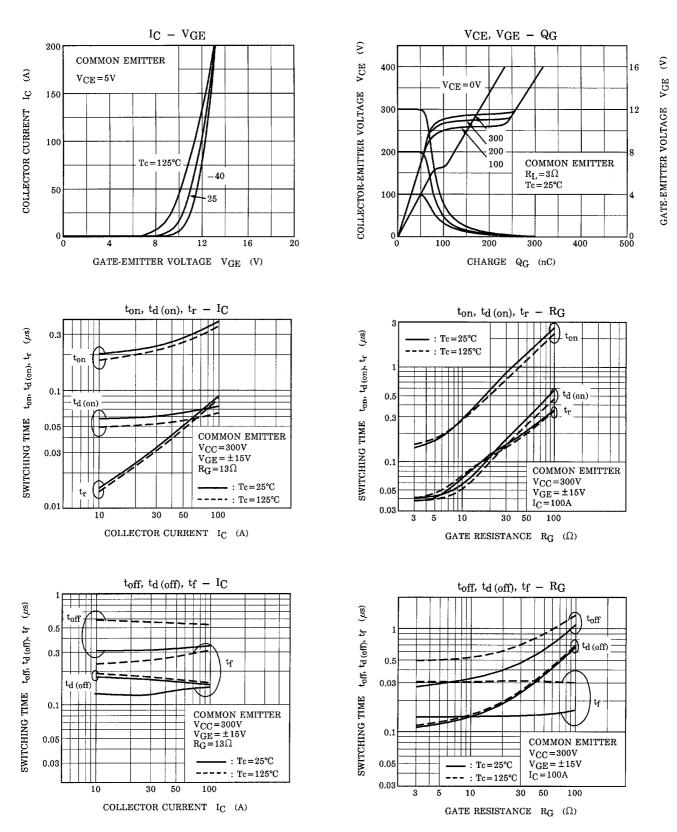
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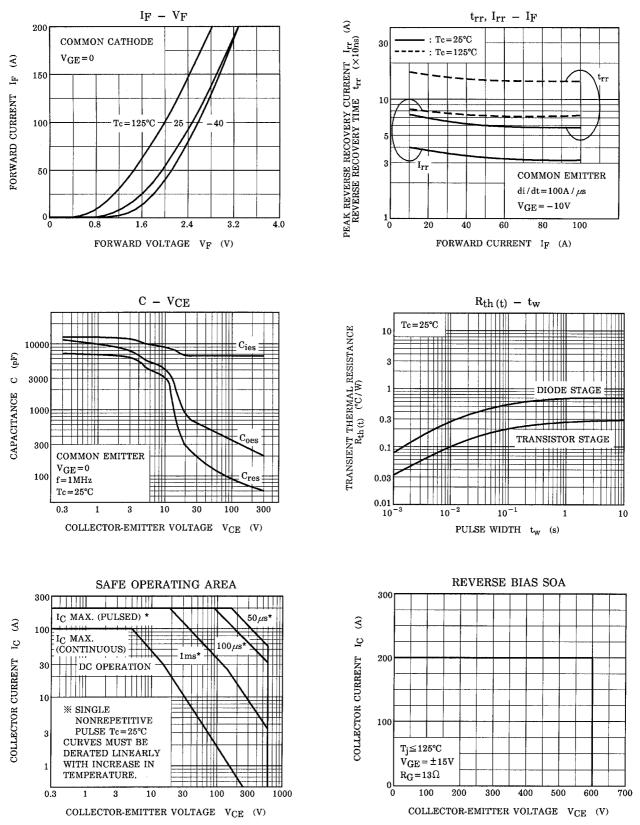


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